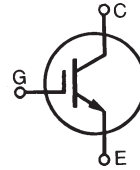


High Voltage IGBT

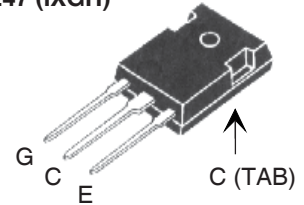
IXGH10N170 IXGT10N170

$V_{CES} = 1700V$
 $I_{C90} = 10A$
 $V_{CE(sat)} \leq 4.0V$

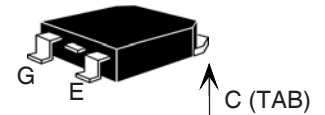


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ C$ to $150^\circ C$	1700	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	20	A
I_{C90}	$T_C = 90^\circ C$	10	A
I_{CM}	$T_C = 25^\circ C$, 1ms	70	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 16\Omega$ Clamped inductive load	$I_{CM} = 20$ @ $0.8 \cdot V_{CES}$	A
P_C	$T_C = 25^\circ C$	110	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 (IXGH)



TO-268 (IXGT)



G = Gate C = Collector
 E = Emitter TAB = Collector

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

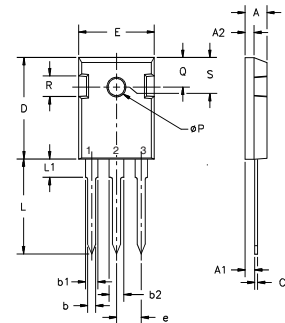
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.7 3.4	4.0 V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 10\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	3.8	6.3	S
$I_{C(ON)}$	$V_{CE} = 10\text{V}, V_{GE} = 10\text{V}$		33	A
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		700	pF
C_{oes}		40	pF	
C_{res}		14	pF	
Q_g	$I_C = 10\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		32	nC
Q_{ge}		4	nC	
Q_{gc}		16	nC	
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$ $I_C = 10\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 850\text{V}, R_G = 16\Omega$		30	ns
t_r		69	ns	
$t_{d(off)}$		132	ns	
t_f		600	ns	
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$ $I_C = 10\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 850\text{V}, R_G = 16\Omega$		30	ns
t_{ri}		270	ns	
$t_{d(off)}$		135	ns	
t_{fi}		495	ns	
R_{thJC}			1.1	$^\circ\text{C/W}$
R_{thCS}	(TO-247)	0.25		$^\circ\text{C/W}$

TO-247 AD Outline

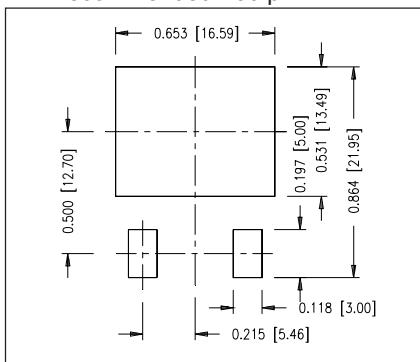


Terminals: 1 - Gate 2 - Drain

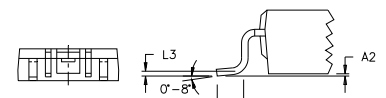
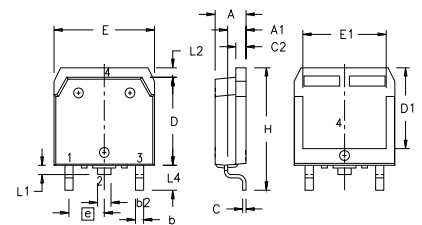
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Min Recommended Footprint



TO-268 Outline



Terminals: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25°C

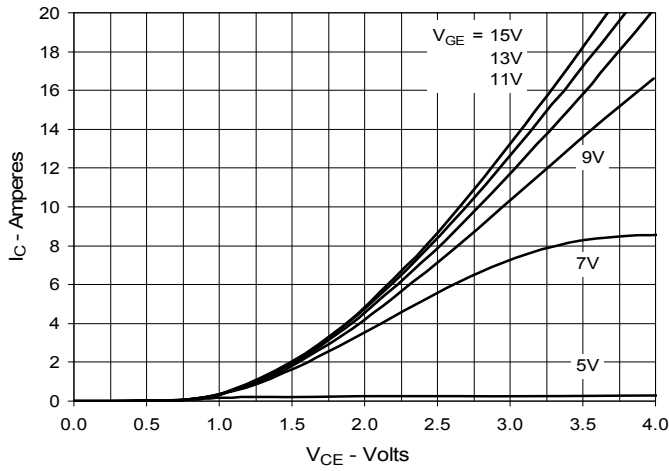


Fig. 2. Extended Output Characteristics @ 25°C

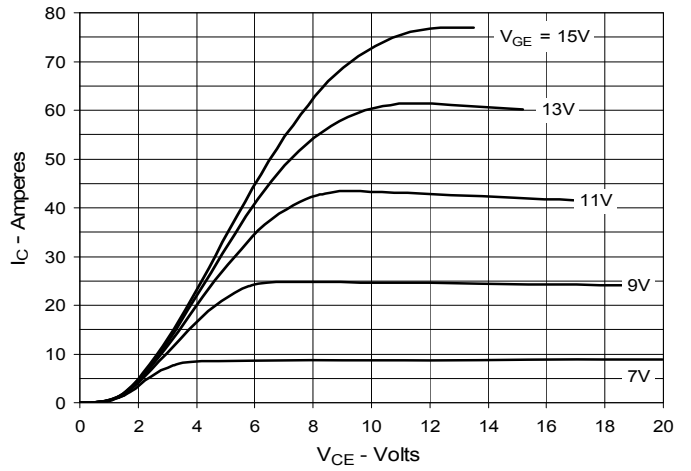


Fig. 3. Output Characteristics @ 125°C

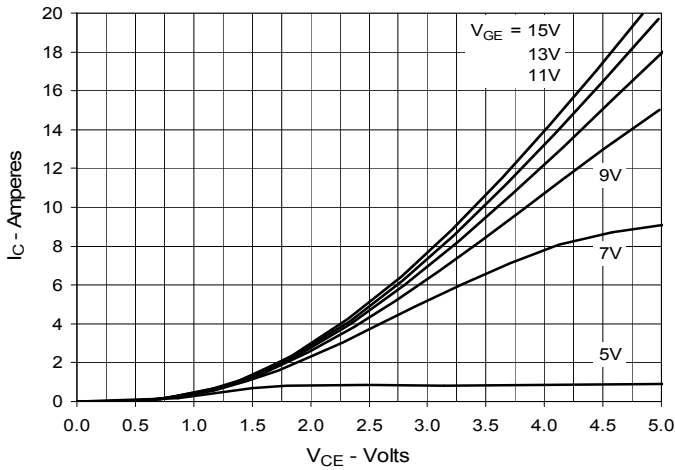


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

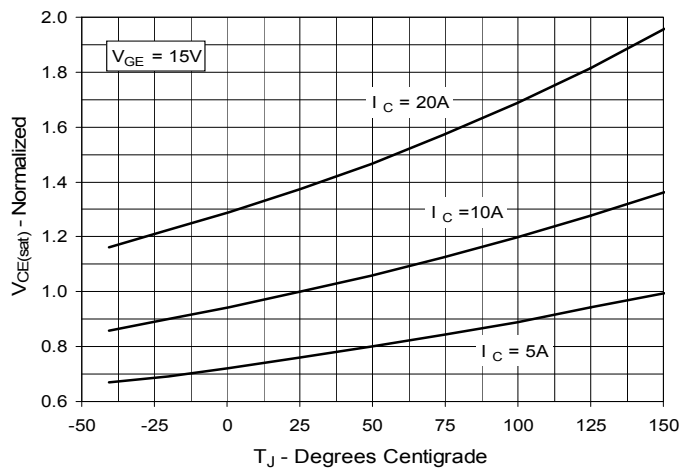


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

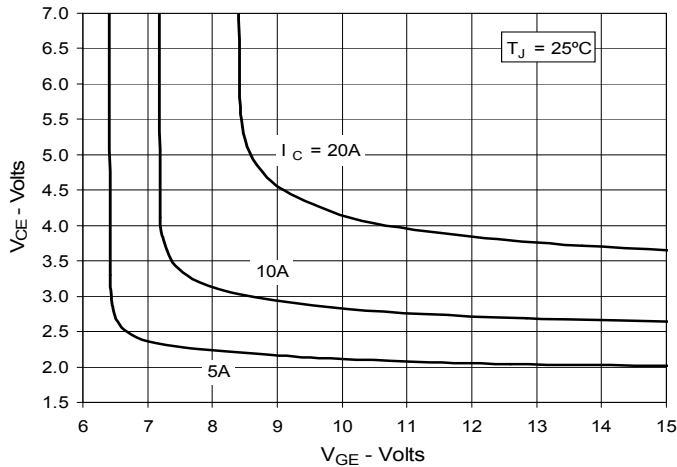


Fig. 6. Input Admittance

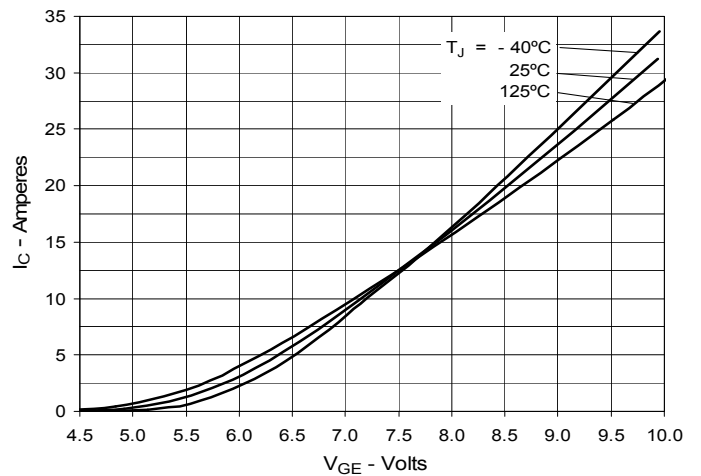


Fig. 7. Transconductance

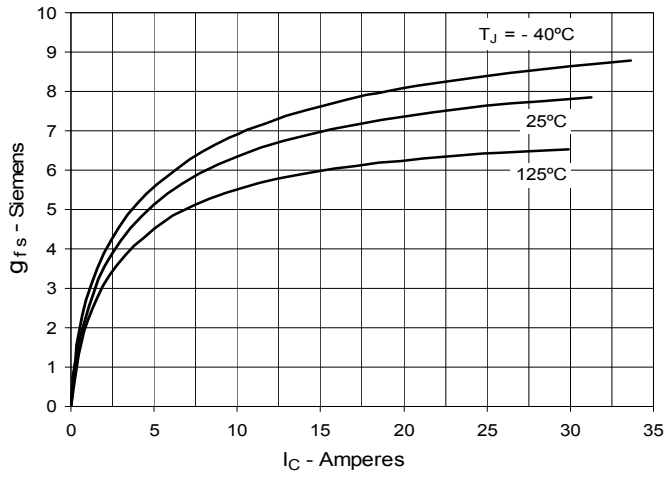


Fig. 8. Gate Charge

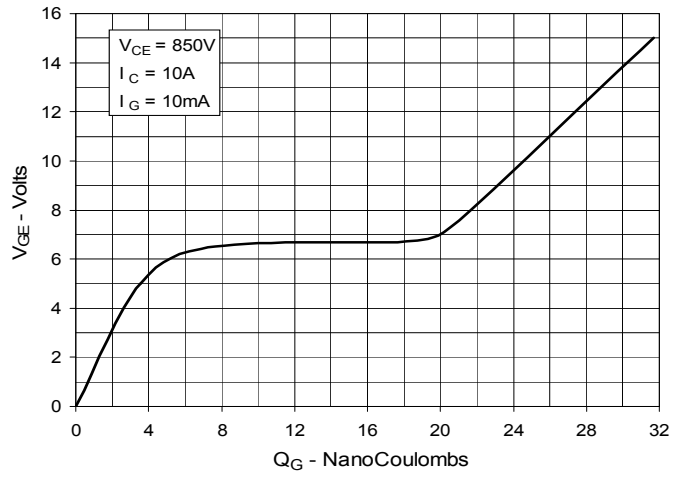


Fig. 9. Reverse-Bias Safe Operating Area

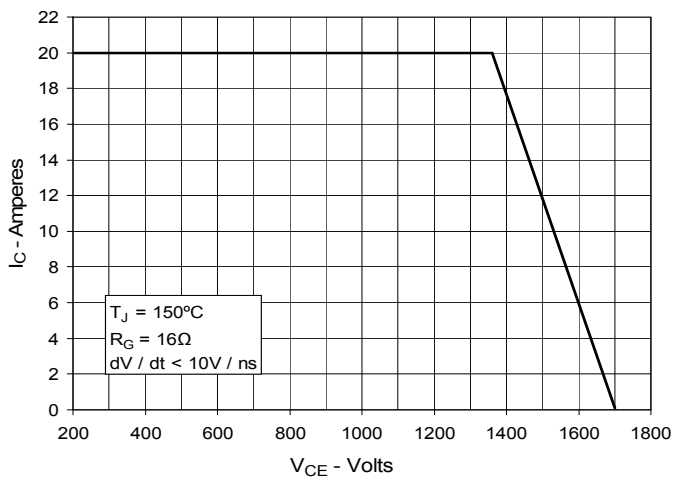


Fig. 10. Capacitance

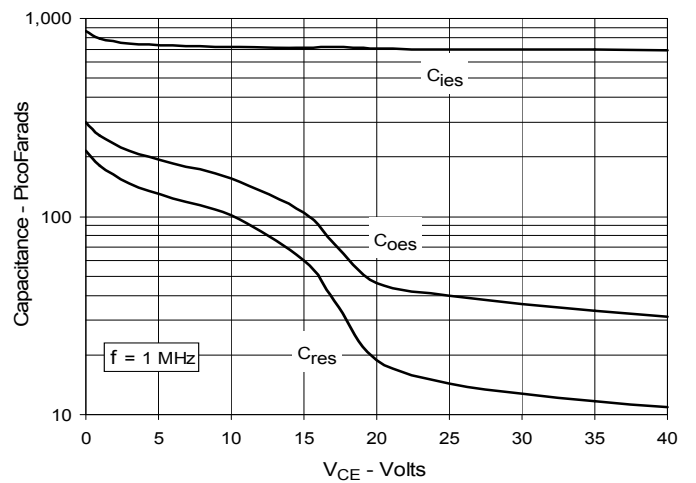


Fig. 11. Maximum Transient Thermal Impedance

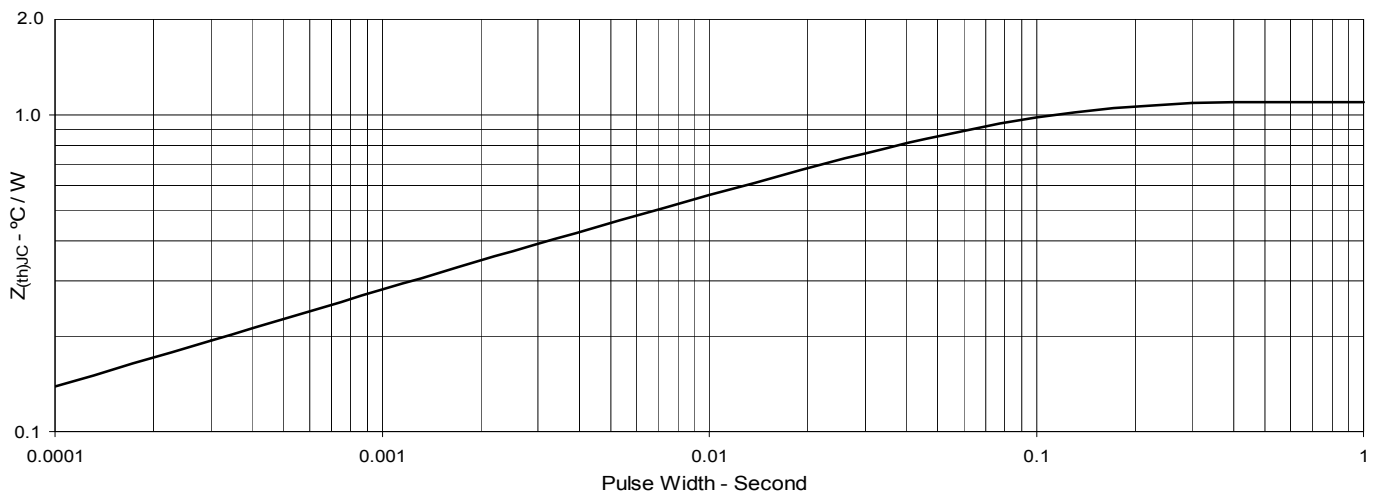


Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

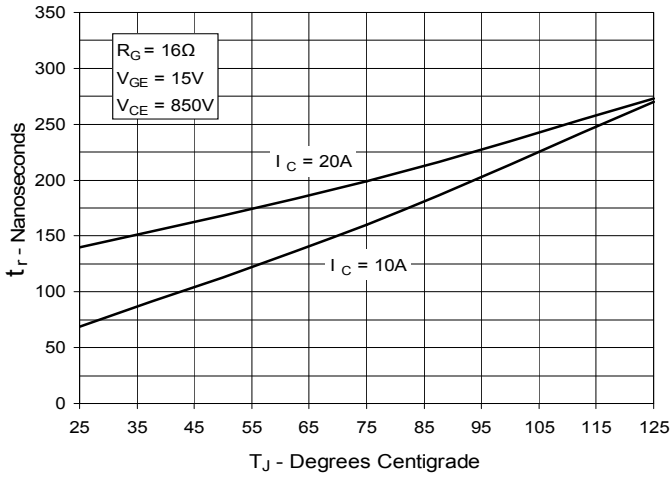


Fig. 13. Resistive Turn-on Rise Time vs. Collector Current

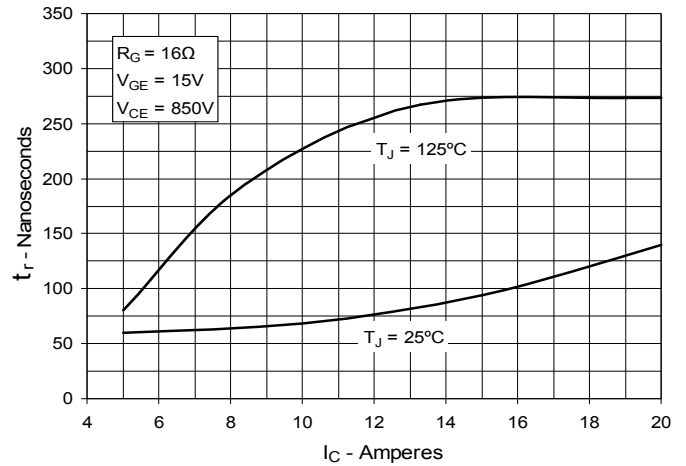


Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

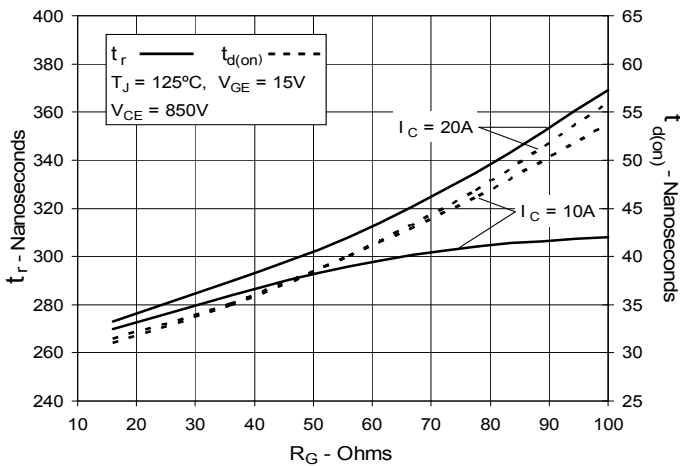


Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

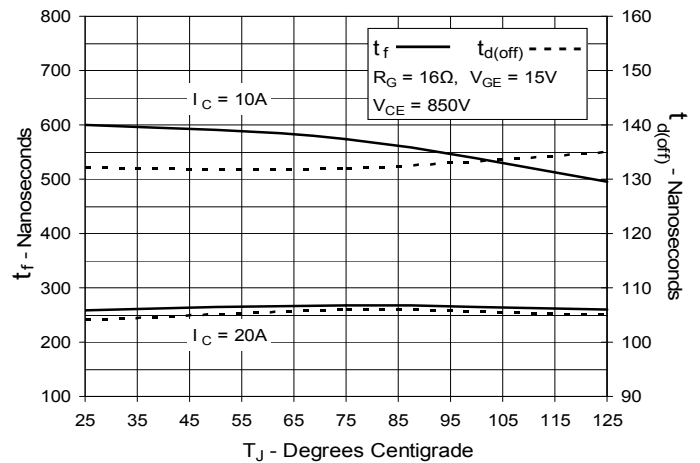


Fig. 16. Resistive Turn-off Switching Times vs. Collector Current

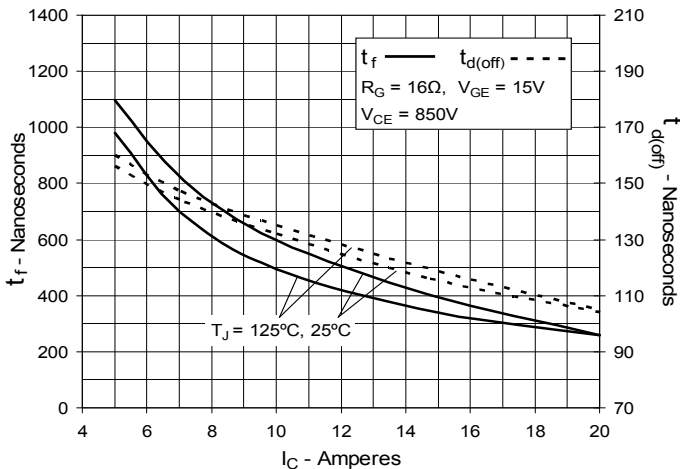


Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance

